

Process flow title:	Pt100 Thin-Film RTD Process	Revision:	Rev 0.1
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## Process Overview

A process flow for fabricating a Pt100 resistance temperature detector (RTD) on oxidized silicon, using Ti/Pt thin films patterned by lift-off.

### Key Specifications

- Substrate: n-type silicon wafer, <100>, with thermal oxide isolation
- Insulating layer: 500 nm thermal SiO<sub>2</sub>
- Adhesion layer: 10 nm Ti
- Sensing layer: 100 nm Pt, patterned in meander geometry
- Nominal resistance: 100 Ω at 0 °C (Pt100)

### Critical Safety

- **HF handling:** Apron + gloves, face shield, no lone working, no glass beakers!
- **Solvents:** Acetone, IPA, resist remover: Use fume hood and PPE.
- **Sputter/evaporation:** Pt/Ti target change requires care; follow target handling SOP
- **Anneal:** Use thermal gloves for > 300 °C operations

## 1 Starting Material

Substrate	Specification	Thickness	Box Name	Qty
Silicon	n-type <100>, 4", 0.025 Ω cm	525 μm ± 20 μm	SN608	5

## 2 Critical Layers

Layer	Material	Thickness
Insulating oxide	Thermal SiO <sub>2</sub>	500 nm
Adhesion layer	Ti	10 nm
Resistive element	Pt	100 nm
Optional pad metallization	Ni/Au	20 nm Ni + 200 nm Au

## 3 Core Process Flow

Table 1: Pt100 RTD Process Flow

Step	Process	Equipment	Parameters	Comment
<b>1</b>	<b>Wafer Prep and Oxide</b>			
1.1	Incoming inspection	4-point probe + thickness tool	Measure resistivity, bow, thickness	Verify starting wafer specs.
1.2	Pre-oxidation clean	RCA bench	Standard RCA clean	Required prior to oxidation.
1.3	Thermal oxide growth	Furnace: E1 oxidation	Target: 500 nm Recipe: WET1100 Oxidation time: 50 min Anneal time: 20 min	Provides electrical isolation.
1.4	Inspection	Ellipsometer		Verify oxide thickness.
<b>2</b>	<b>Lithography</b>			

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Table 1: Pt100 RTD Process Flow (Continued)

Step	Process	Equipment	Parameters	Comment
2.5	Develop	TMAH lithography	UV-Developer: AZ 726 MIF Time: 60 s to 75 s, gentle agitation Rinse: DI water, 30 s	Creates undercut profile for lift-off.
<b>3 Metal Deposition</b>				
3.1	Chamber prep	Temescal e-beam evaporator	Base pressure $\leq 1 \times 10^{-6}$ mbar	Lift-off friendly.
3.2	Ti deposition	Temescal	10 nm Ti @ 0.5 Å/s to 1 Å/s	Adhesion layer.
3.3	Pt deposition	Temescal	100 nm Pt @ 1 Å/s to 2 Å/s	Resistive layer.
<b>4 Lift-off</b>				
4.1	Lift-off	Solvent bath (acetone)	Soak + ultrasonic assist if needed	Leaves Ti/Pt meander.
4.2	Rinse/Dry	IPA + N2 gun		Inspect for clean edges, no flakes.
<b>5 Post-processing (optional)</b>				
5.1	Optional anneal	C3 Furnace: N <sub>2</sub> ambient	400 °C, 1 h	Stabilizes Pt resistance.
5.2	Optional pad metallization	Lithography + evaporation	Ni/Au stack	Improves bondability.
5.3	Final inspection	Optical microscope + 4-point probe	Measure sheet R, continuity	Target $R = 100 \Omega$ at 0 °C.

## 4 Critical Checks

Step	QC Verification
1.3	Oxide thickness: 200 nm $\pm$ 10 nm (ellipsometer)
2.2	Lithography: line/space $\pm$ 1 $\mu$ m (optical inspection)
3.3	Pt thickness: 100 nm $\pm$ 5 nm (Dektak XTA stylus profiler)
4.1	Lift-off complete, no bridging (microscope)
5.1	Sheet resistance stable within 1% after anneal (4-point probe)

## 5 Process Flow Diagram

Figure 1: Process flow diagram for Pt100 RTD fabrication.

## 6 Required Figures

Table 2: Cross-sectional illustrations of key process steps in the Pt100 RTD fabrication flow.

ID	Step	Description
1	1.3	Thermal oxide isolation
2	2.2	Lithography defines meander
3	3.3	Ti/Pt deposition
4	4.1	Lift-off completed
5	5.1	Optional anneal / pad metallization